

Radiation Effects on Solar Cell

BTP Project 2025

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Under the guidance of

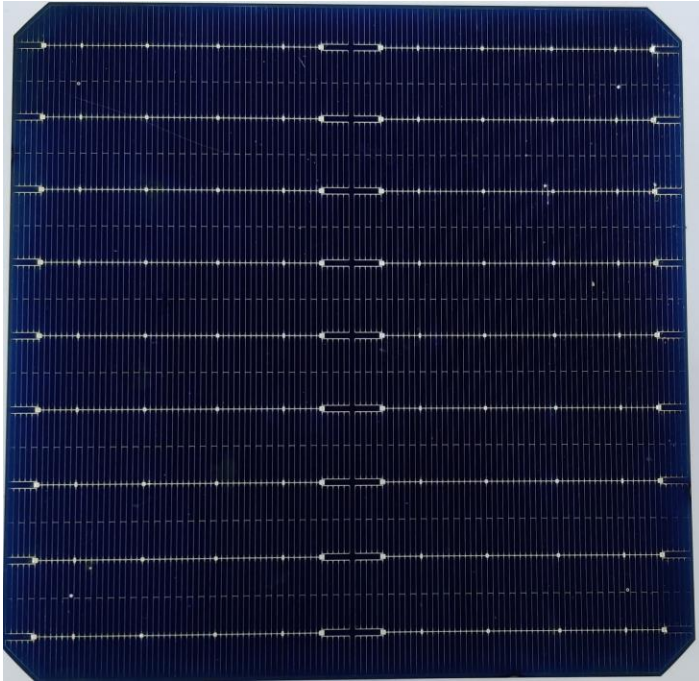
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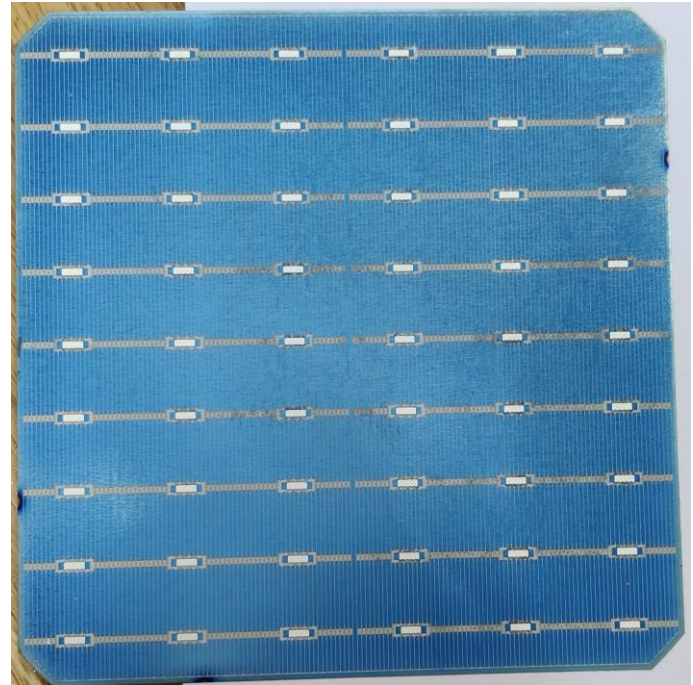
Introduction

Given a PV solar array:

The task is to accurately measure I-V characteristics of the solar array.



Top plate

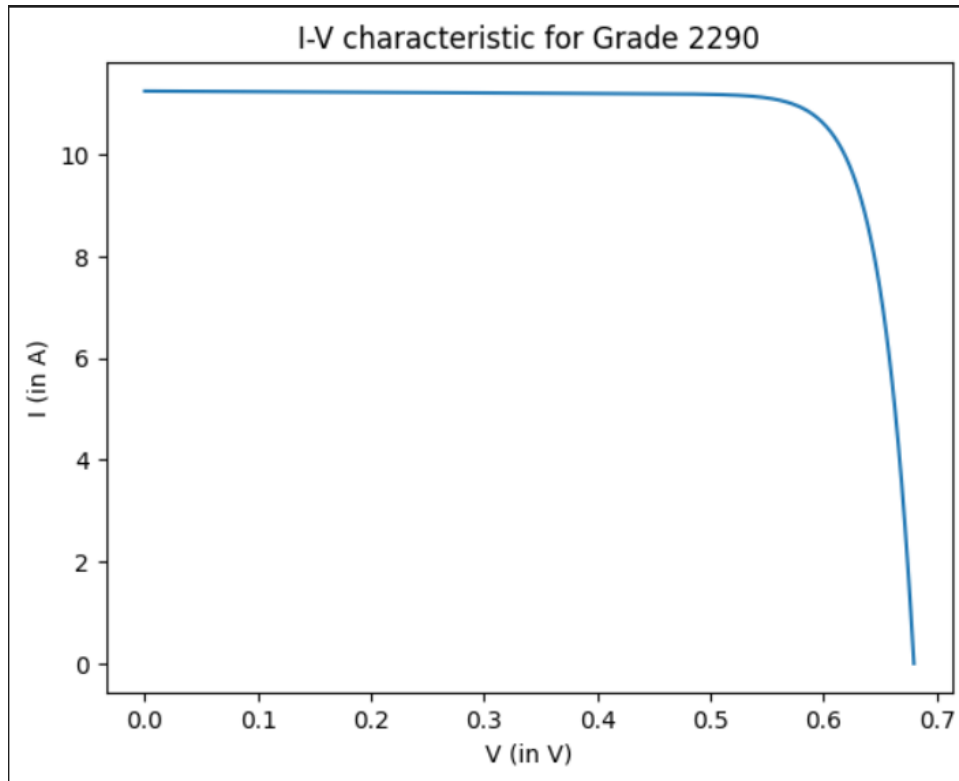


Bottom plate

What problem are we trying to solve?

Given a PV solar array:

The problem is to accurately measure I-V characteristics of the solar array.

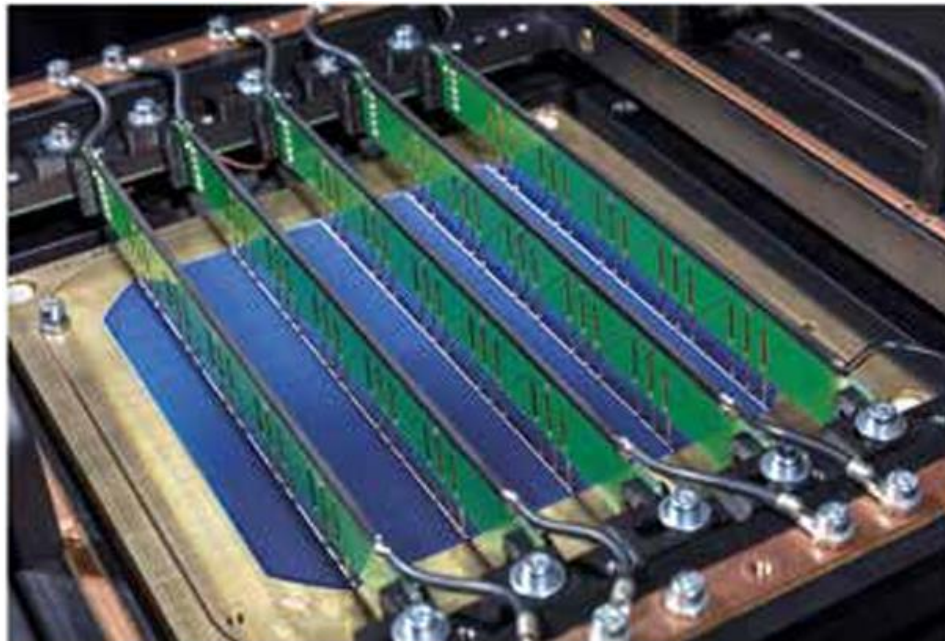


The given plot is the ideal IV characteristics that is required to be captured through the hardware

Hardware Setup

The probing method used at present:

- Top plate has 9 bus bars from which voltage and current probes (pogo pins) are taken.
- The configuration of one bus bar PCB is: 6 Current tabs and 1 Voltage tab.

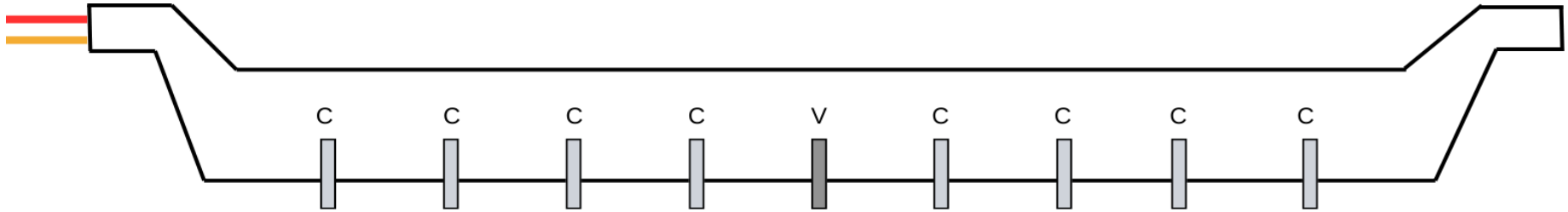


PV solar array with bus bars
PCBs [1]

[1] - Bothe, K., & Hinken, D. (2019). Precise and accurate solar cell measurements at ISFH CalTeC. *Photovoltaics International*, 43, 74-81

Probing Setup - Top

The probing method used at present:

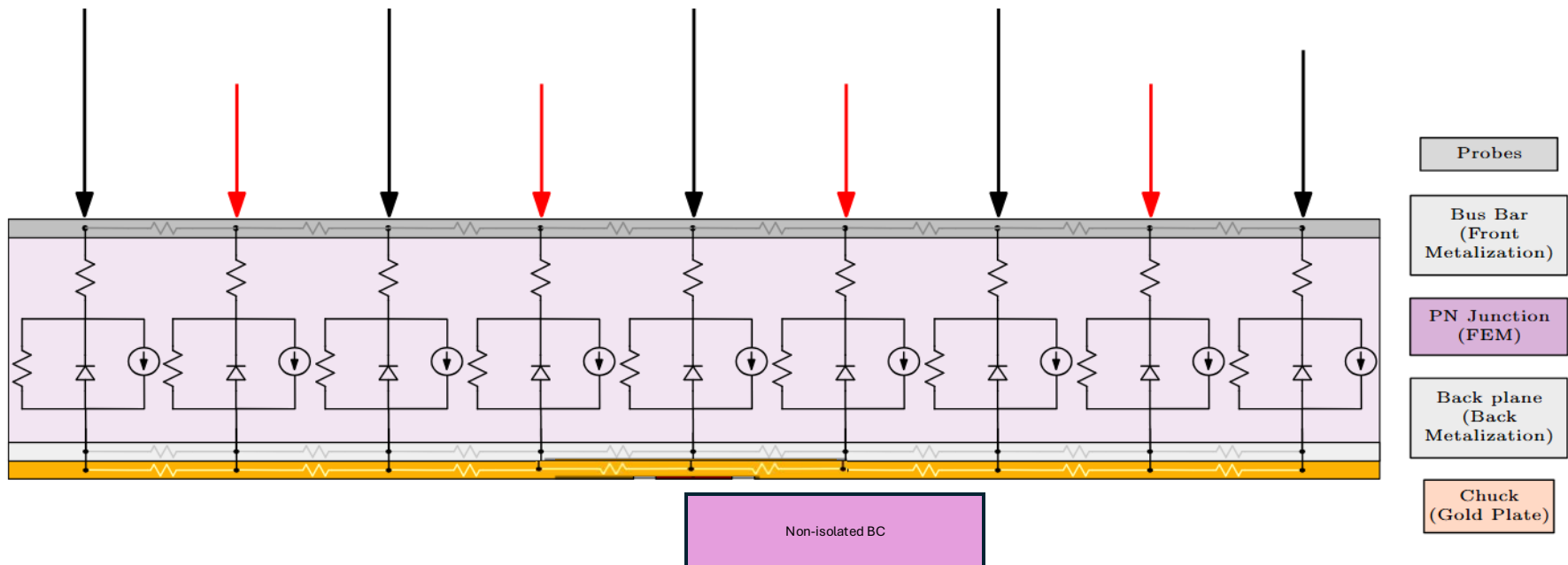


- The probe bar shown above is placed on all bus bars on top plate.
- All the current tabs are shorted and taken out from Yellow wire across all probe bars.
- Voltage tab is taken out from using Red wire and shorted across all probe bars.

Probing Setup - Bottom

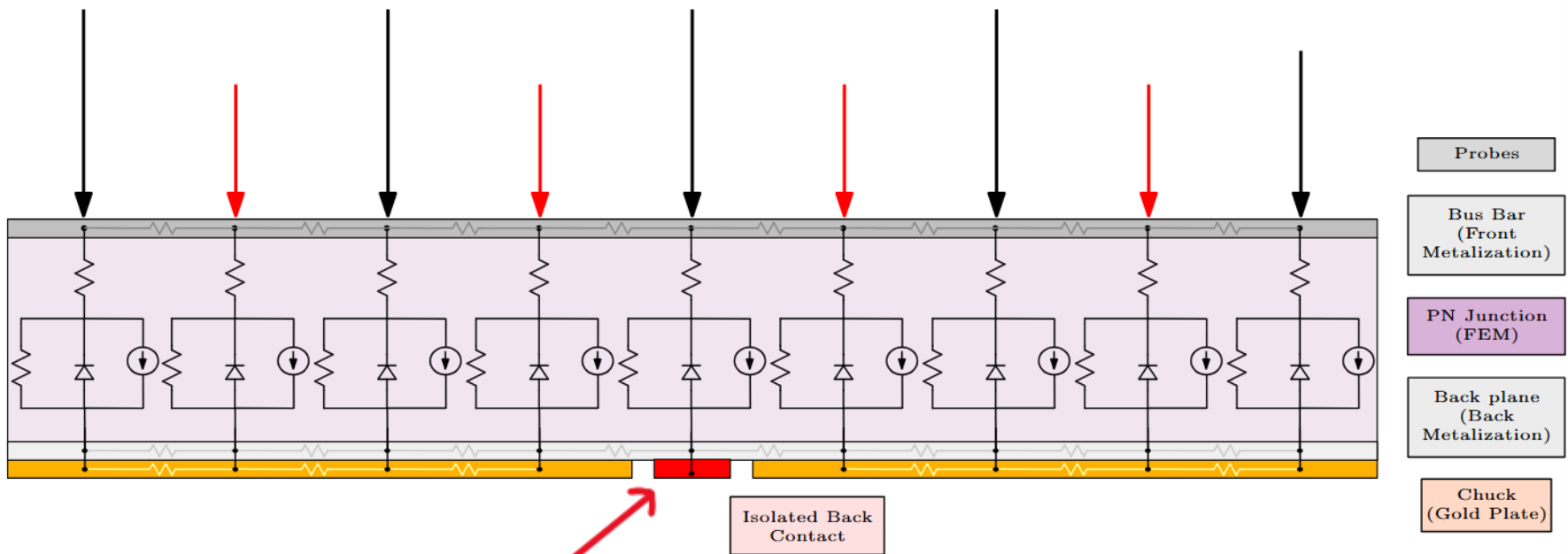
Back Contact configurations:

The comparison has to be made: **With isolated VS Without isolated back contact** to check if the isolated back contact is yielding a better result.



Probing Setup - Bottom

Back Contact configurations:



For isolated back contact the bottom probed directly touches the bottom of solar cell

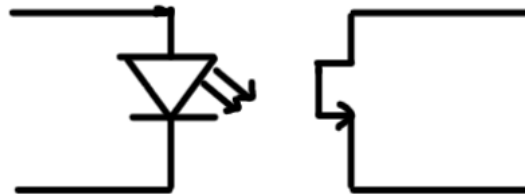
Problem Statement and Approach

The options available are:

1. Make **hardware changes** to yield better IV characteristics
2. Modify **Measurement circuitry**
3. Compare **Isolated and Non-isolated Back contact**

Approaches:

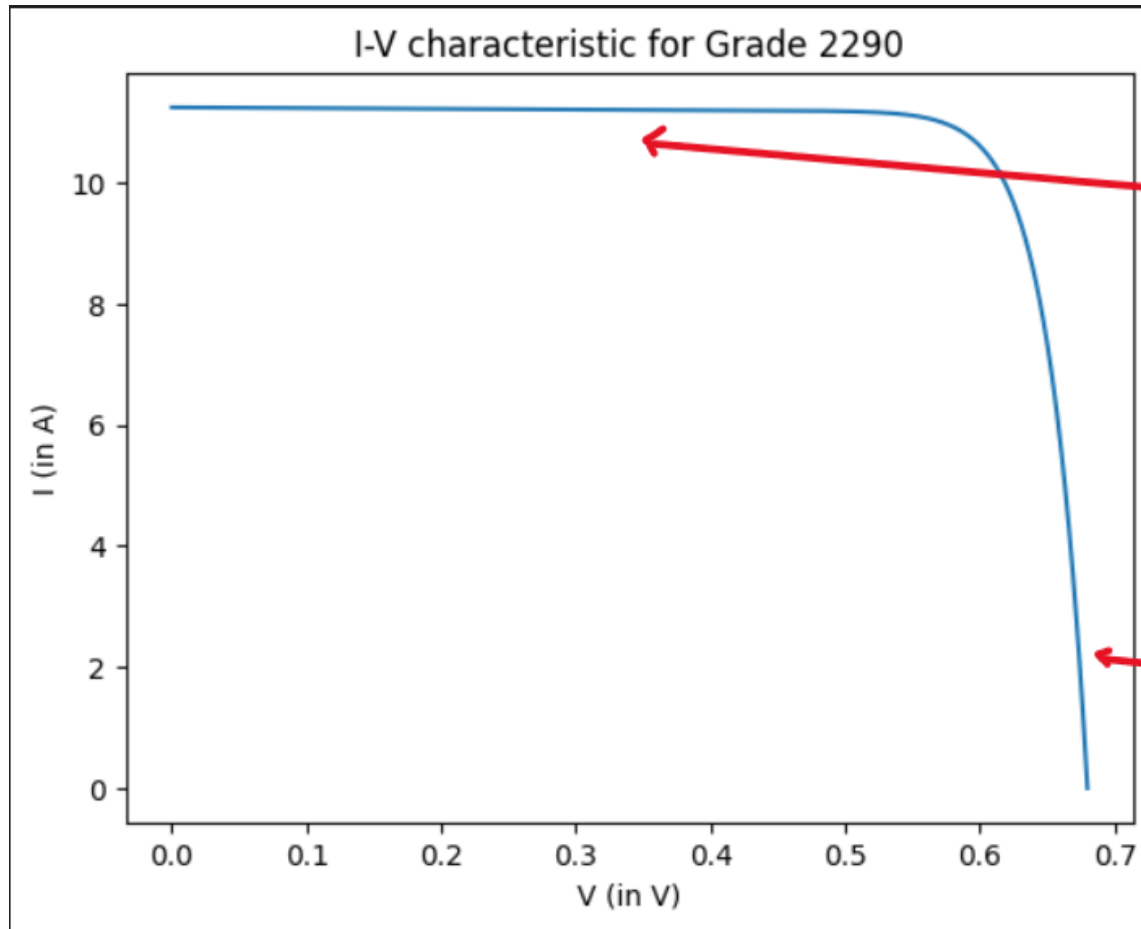
1. The probing contacts can be **galvanically isolated** in order to avoid ground looping
2. Electrically **isolating Power & Measurement circuit** to avoid ground looping
 - Opto-coupled OPAMPS are used to achieve isolation



- There are Opto-coupled OPAMP ICs available like AMC1200, AMC1211, etc...
3. Simulate the complete setup with **different back contact configuration**

METHODOLOGY – I (ELECTRICAL ISOLATION)

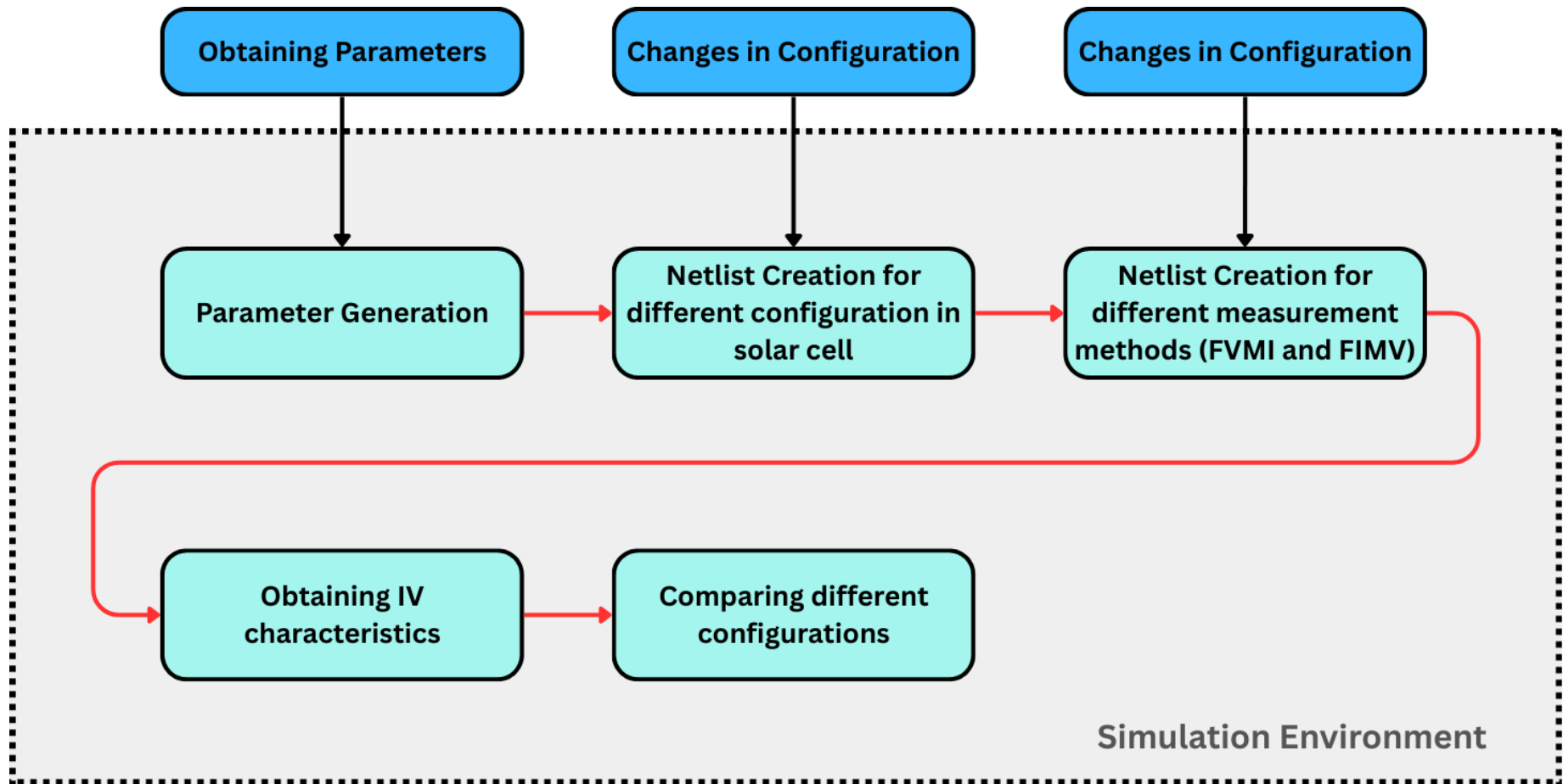
Isolation is critical when measuring low resistances as claimed by Megger in 'A guide to low resistance testing'



$$\frac{\delta I}{\delta V} \rightarrow 0$$
$$\Rightarrow R \rightarrow \infty$$

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$$\Rightarrow R \rightarrow 0$$

METHODOLOGY – II (SIMULATION CHECK)

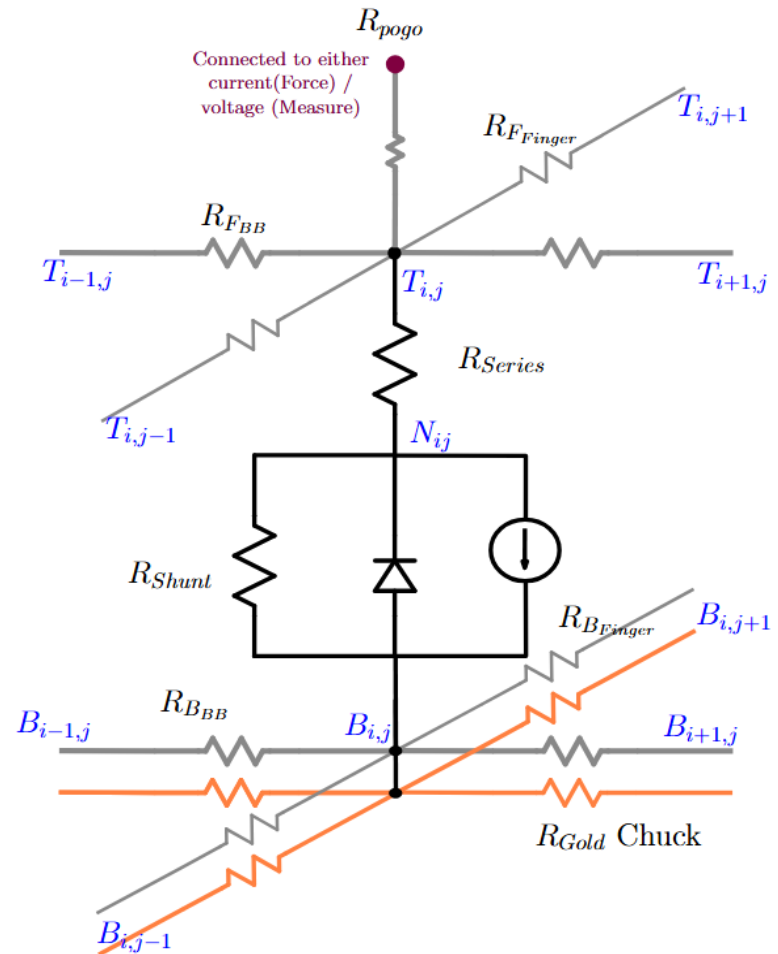


METHODOLOGY – II (SIMULATION CHECK)

Finite Element Model of Simulation:

A ($m \times n$) resistance mesh grid is constructed, where m represents the number of bus bars and n denotes the number of fingers.

The finite element model incorporates a PN junction, represented by its equivalent circuit, which is connected to the grid nodes. Specific points are probed at the top nodes and designated as either force points or measurement points.



METHODOLOGY – II (SIMULATION CHECK)

Obtaining Parameters:

Busbars and fingers in 9BB solar cell

The provided 9BB solar cell has **9 busbars** and **120 fingers** with an overall dimension of 162mm × 162mm.

- Length of finger enclosed by adjacent busbars is 16.2mm
- Length of busbar enclosed by adjacent fingers is 1.34mm

The parameter that are required to be used in the LTSpice modelling are to be measured and estimated are shown below:

- ① R_{busbar} measurement for metallization
- ② R_{finger} measurement for metallization
- ③ R_{series} of solar cell
- ④ R_{shunt} of solar cell
- ⑤ Chuck resistance estimation
- ⑥ $R_{pogopin}$ measurement

METHODOLOGY – II (SIMULATION CHECK)

Obtaining Parameters: R_busbar metallization

Measurement method

Resistance per unit length ($m\Omega/mm$) is found using Multimeter

- For a length of 1.35mm on **front plate**, resistance per unit length varies between (40-60) $m\Omega/mm$ with a mean value of occurrence as 41.2 $m\Omega/mm$.
- For a length of 1.1mm on **bottom plate**, resistance per unit length varies between (5-7) $m\Omega/mm$ with a mean value of occurrence as 6 $m\Omega/mm$.
- Resistance of **busbar on front plate** enclosed by adjacent fingers is $1.34mm \times 41.2m\Omega/mm = 55.208m\Omega$.
- Resistance of **busbar on bottom plate** enclosed by adjacent fingers is $1.34mm \times 6m\Omega/mm = 8.04m\Omega$.

METHODOLOGY – II (SIMULATION CHECK)

Obtaining Parameters: R_finger metallization

Measurement method

Resistance per unit length ($m\Omega/mm$) is found using Multimeter

- For a length of 17.2mm on **front plate**, resistance per unit length varies between (80-120) $m\Omega/mm$ with a mean value of occurrence as 89 $m\Omega/mm$.
- For a length of 17.5mm on **bottom plate**, resistance per unit length varies between (40-60) $m\Omega/mm$ with a mean value of occurrence as 51.11 $m\Omega/mm$.
- Resistance of **finger on front plate** enclosed by adjacent busbar is $16.2mm \times 89m\Omega/mm = 1.4418\Omega$.
- Resistance of **finger on bottom plate** enclosed by adjacent busbar is $16.2mm \times 51.11m\Omega/mm = 0.8279\Omega$.

METHODOLOGY – II (SIMULATION CHECK)

Obtaining Parameters: R_series and R_shunt with infinitesimal I

The parameters such as IFEM, Rshunt and Rseries for the infinitesimal model are deduced from the parameter extraction method used from the **shape parameters (m and y parameters)** of the solar panel datasheet and current extraction approach from given parameters in datasheet.

- V_{OC} : Open circuit voltage (in V)
- I_{SC} : Short circuit current (in A)
- V_{mp} : Voltage at maximum power point (in V)
- I_{mp} : Current at maximum power point (in A)
- P_{mp} : Power at maximum power point (in W)
- *Efficiency* : Efficiency of solar to electrical energy conversion
- T : Temperature of PV solar array (in $^{\circ}C$)
- *Area* : Area of PV solar array (in cm^2)

$$FF = v_p j_p$$

$$m \log(v_p) + \log(m + 1) = 0$$

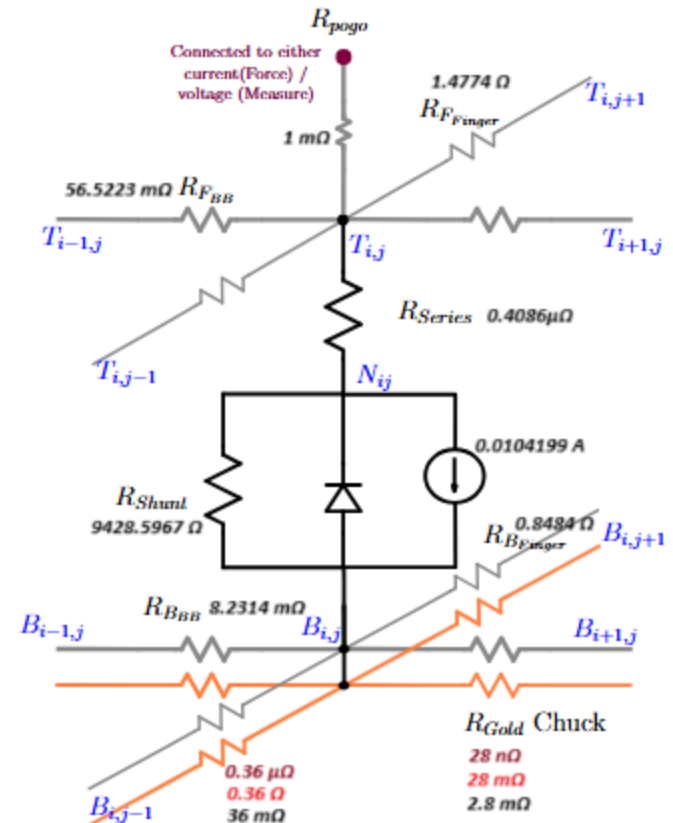
$$v_p [1 - (1 - \gamma)v_p - \gamma v_p^m] - FF = 0$$

METHODOLOGY – II (SIMULATION CHECK)

Obtaining Parameters:

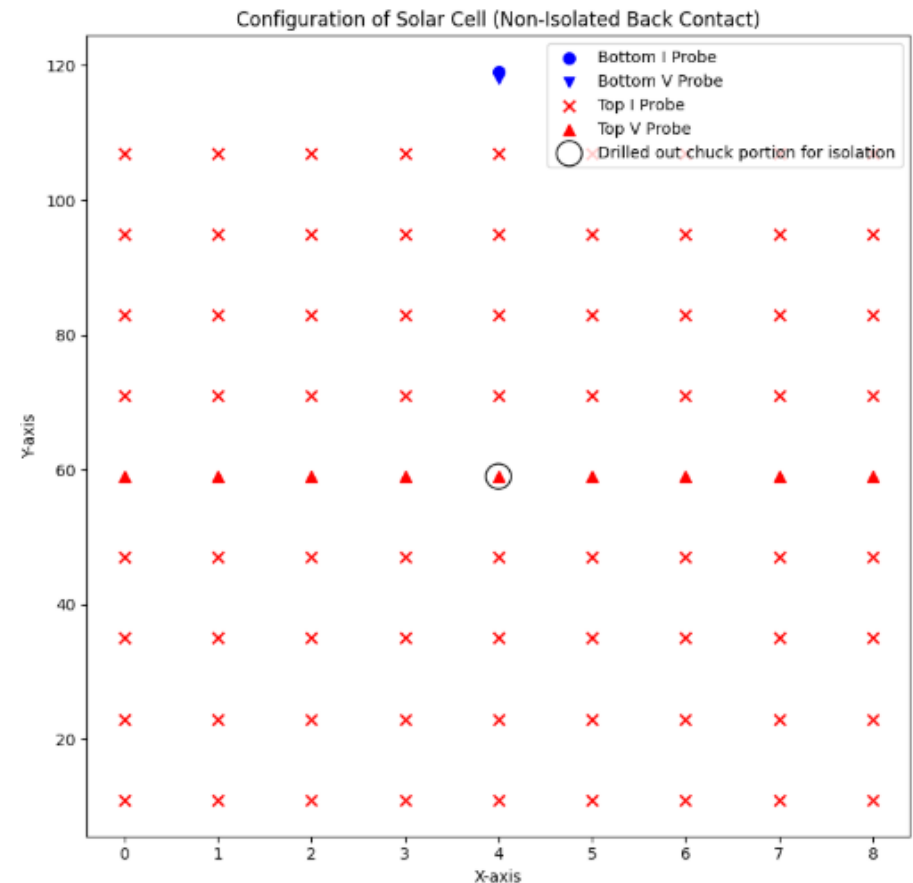
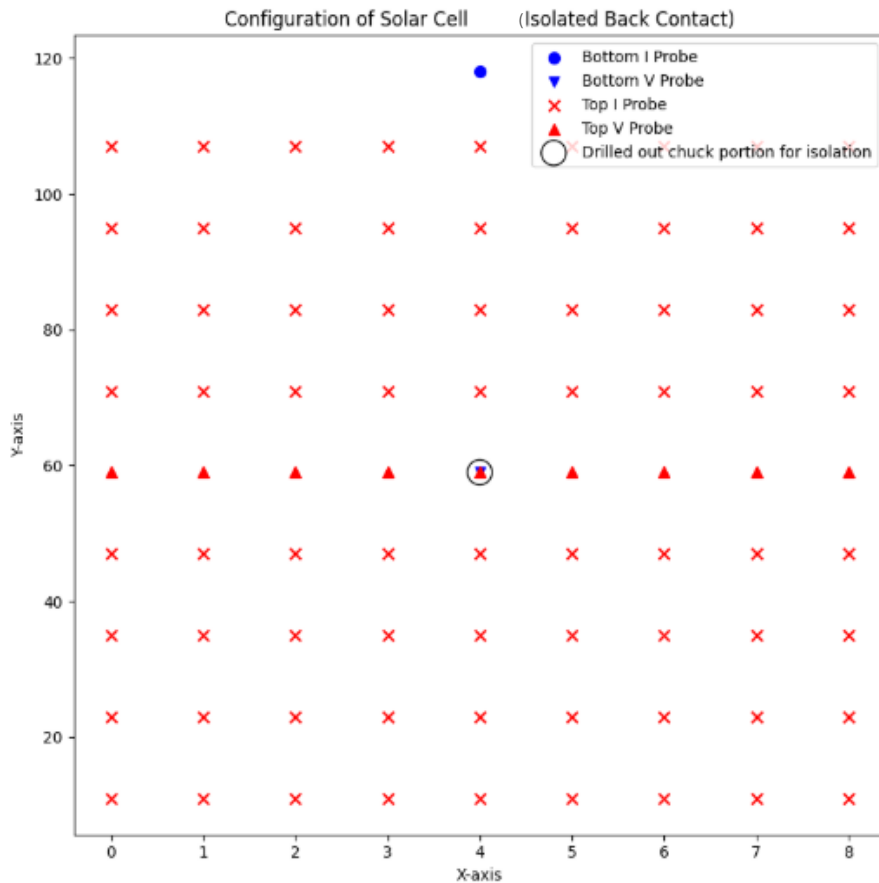
The parameter obtained or estimated are mentioned in the Finite Element Model of the solar cell as shown.

The values of Gold chuck resistance is **not known**, so different values are used to obtain the **best fit**.



METHODOLOGY – II (SIMULATION CHECK)

Configurations: *With isolated and without isolated back contact*



METHODOLOGY – II (SIMULATION CHECK)

Simulation circuit netlist:

Measurement methods of ***Force Current Measure Voltage (FIMV)*** and ***Force Voltage Measure Current (FVMI)*** are used for each configuration setup in simulation.

(I) Force Current Measure Voltage (FIMV):

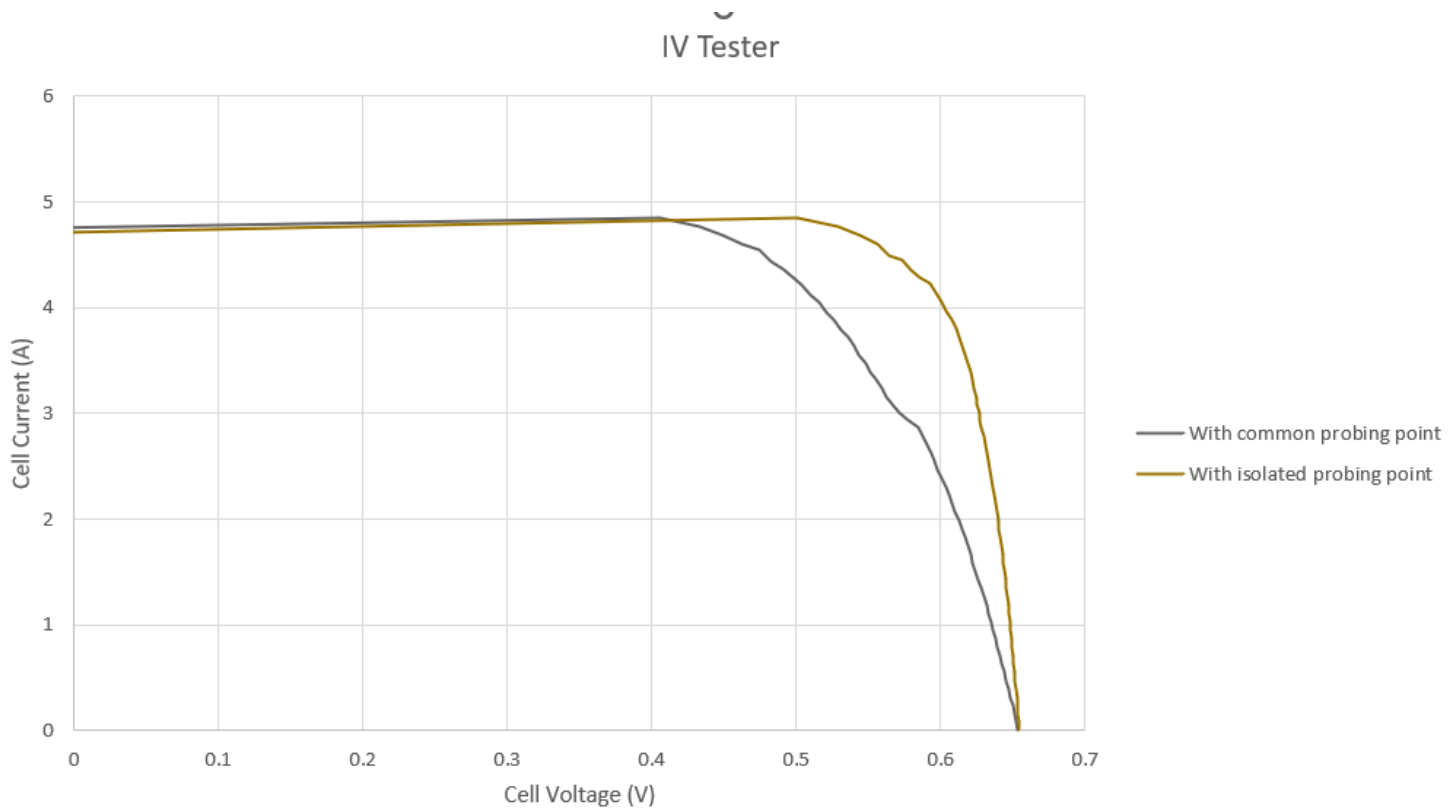
Voltage controlled current source is established with negative feedbacked loop to maintain desired voltage in the power circuit

(II) Force Voltage Measure Current (FVMI):

Current controlled current source is established with negative feedbacked loop to maintain desired current in the power circuit

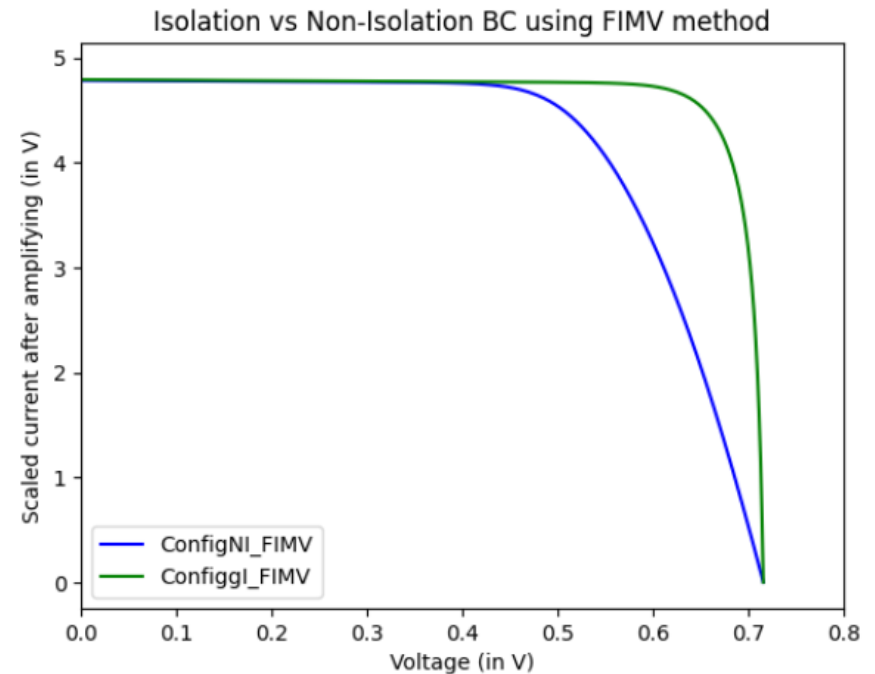
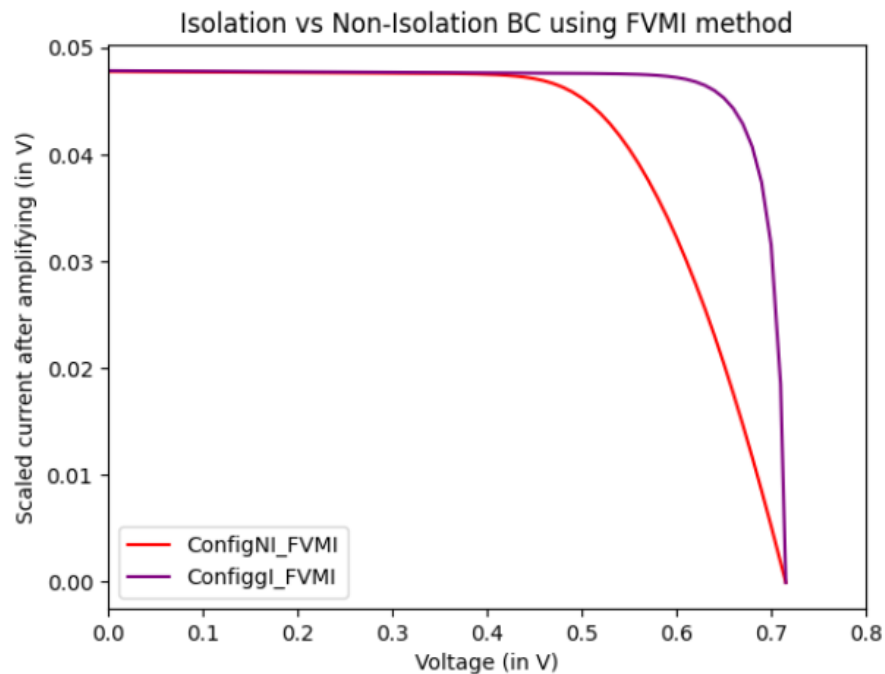
METHODOLOGY – II (SIMULATION CHECK)

With isolated and without isolated back contact configurations are made in hardware and the IV characteristics are captured to be:



METHODOLOGY – II (SIMULATION CHECK)

Comparison of Isolated and Non-isolated Back contact:



METHODOLOGY – III (Gold Resistance Fit)

Iterative Approach to Estimate Gold Chuck Resistance:

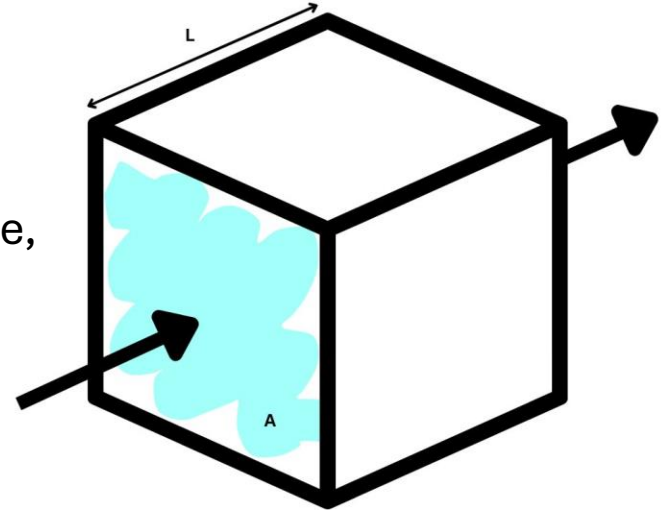
Why Estimate Gold Chuck Resistance?

- Accurate resistance modeling is essential for realistic IV curve simulation.
- Direct calculation of mesh resistance from sheet resistance is challenging due to:
 - Fine grid structure
 - Non-uniform contact areas
 - Complex current paths

What to consider as a reference?

By finding the equivalent Resistance from side-to-side, and having it as the reference

$$R_{side-to-side} = \frac{\rho L}{A}$$



METHODOLOGY – III (Gold Resistance Fit)

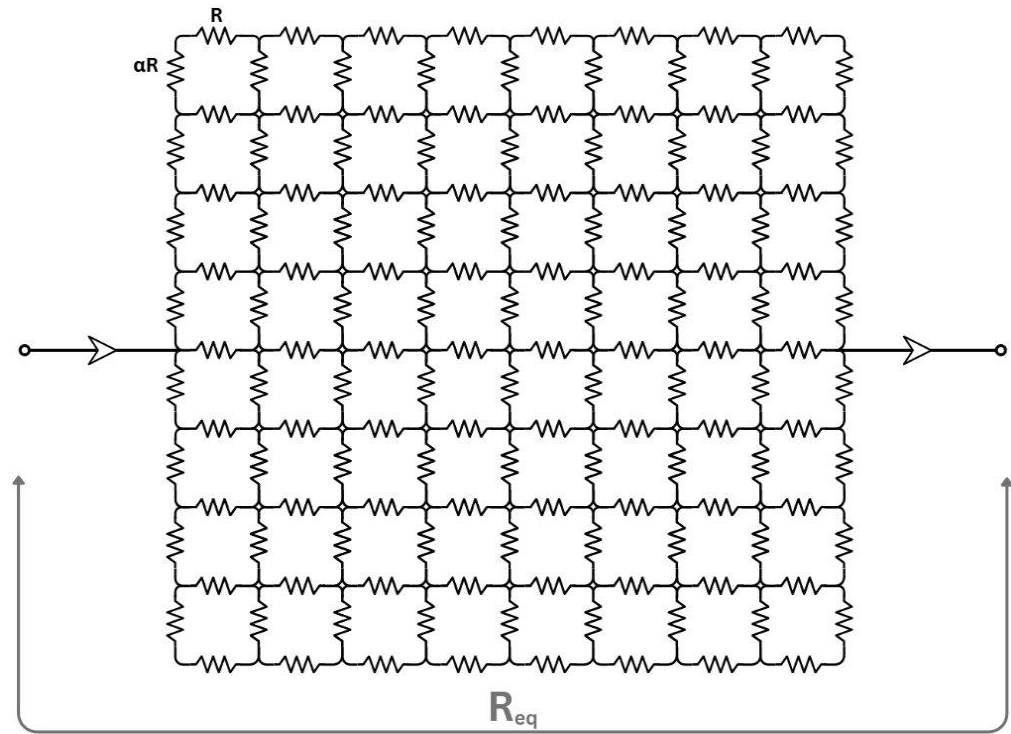
Iterative Approach to Estimate Gold Chuck Resistance:

How to find infinitesimal resistance?

- Create a mesh network in LTspice and apply a unit current to measure voltage.
- Adjust resistance per unit length iteratively until the simulated side-to-side resistance matches the analytical value.

Python-LTspice Integration:

- Automates netlist generation, simulation, and result comparison.
- Updates resistance values efficiently to ensure accurate modeling of the gold chuck.



Conclusion

Results:

1. The parameters found or estimated are provided below:

Parameter Name	Symbol	Value / Random Interval
Top Finger Resistance	$R_{\text{top-finger}}$	1.376 Ω to 2.064 Ω
Top Busbar Resistance	$R_{\text{top-busbar}}$	0.06075 Ω to 0.108 Ω
Bottom Finger Resistance	$R_{\text{bottom-finger}}$	0.7 Ω to 1.05 Ω
Bottom Busbar Resistance	$R_{\text{bottom-busbar}}$	0.0055 Ω to 0.0077 Ω
Chuck Finger Resistance	$R_{\text{chuck-finger}}$	0.35 Ω to 0.37 Ω
Chuck Busbar Resistance	$R_{\text{chuck-busbar}}$	0.027 Ω to 0.029 Ω
Shunt Resistance	R_{shunt}	9800 Ω to 10000 Ω
Series Resistance	R_{series}	$4.25 \times 10^{-7} \Omega$ to $4.3 \times 10^{-7} \Omega$
Pogo Pin Resistance	R_{pogo}	1 m Ω (fixed)
Illumination Current	I_{FEM}	0.01047087 A (fixed)

2. The estimated order of gold chuck resistances are 28m Ω for busbar and 0.36 Ω for finger.

Conclusion:

1. Accurate IV measurement in solar cells requires proper contact isolation, especially at low resistance regions.
2. Isolated back contact significantly improves measurement accuracy compared to non-isolated setups.
3. For gold chuck, resistance estimate close to the resistance of bottom plate yields an accurate depiction of experimental observation.

Acknowledgment

I would like to express my sincere gratitude to **Dr. Arvind Ajoy**, under whose guidance I completed this project.

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Thank You